N-CHANNEL MOSFET /N沟道增强型场效应晶体管
RCP100N8F6A/RCS100N8F6A/RCD100N8F6A

主要参数 MAIN CHARACTERISTICS

ID	120A
VDSS	85 V
Rdson-typ（ @Vgs=10V）	5.3 mΩ
Qg-typ	67nC

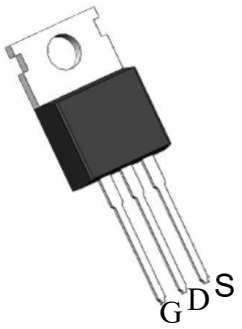
产品特性 FEATURES

低栅极电荷	Low gate charge
开关速度快	Fast switching
100%经过 Rg 测试	100% Rg tested
100%经过雪崩测试	100% avalanche tested
100%经过热阻测试	100% DVDS tested
SGT 工艺	SGT technology
RoHS 产品	RoHS product

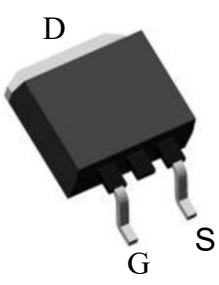
用途 APPLICATIONS

电池管理系统	BMS
电机控制和驱动	Motor control and drive
不间断电源	UPS
开关电源	Switch Mode Power Supplies

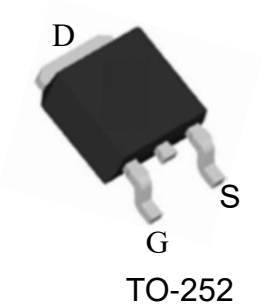
封装形式 Package



TO-220
RCP series

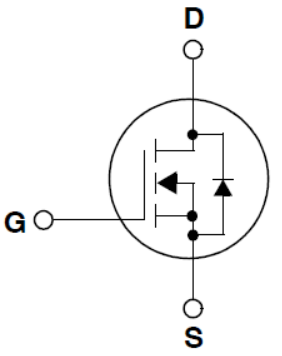


TO-263
RCS series



TO-252
RCD series

等效电路 Equivalent Circuit



绝对最大额定值 ABSOLUTE RATINGS (Tc=25℃)

项目 **Parameter**	符号 **Symbol**	数值 **Value**		单位 **Unit**
		RCP/D100N8F6A	**RCS100N8F6A**	
最高漏极一源极直流电压 Drain-Source Voltage	V_{DS}	85		V
连续漏极电流* Drain Current -continuous *	I_D（T_C=25℃），Silicon Limited	120		A
	I_D（T_C=25℃）,Package Limited	80		A
	I_D（T_C=100℃），Silicon Limited	56		A
最大脉冲漏极电流（注 1） Drain Current – pulse（note 1）	I_{DM}	320		A
最高栅源电压 Gate-Source Voltage	V_{GS}	±20		V
单脉冲雪崩能量（注 2） Single Pulsed Avalanche Energy（note 2）	E_{AS}	200		mJ
雪崩电流（注 1） Avalanche Current（note 1）	I_{AR}	20		A
重复雪崩能量（注 1） Repetitive Avalanche Current（note 1）	E_{AR}	16		mJ
二极管反向恢复最大电压变化速率（注 3） Peak Diode Recovery dv/dt（note 3）	dv/dt	5.0		V/ns
耗散功率 Power Dissipation	P_D （TC=25℃）	156		W
	-Derate above 25℃	1.25		W/℃
最高结温及存储温度 Operating and Storage Temperature Range	T_J，T_{STG}	-55～+150		℃
引线最高焊接温度 Maximum Lead Temperature for Soldering Purposes	T_L	300		℃

*漏极电流由最高结温限制

*Drain current limited by maximum junction temperature

N-CHANNEL MOSFET /N沟道增强型场效应晶体管
RCP100N8F6A/RCS100N8F6A/RCD100N8F6A

电特性 ELECTRICAL CHARACTERISTICS

项目 **Parameter**	符号 **Symbol**	测试条件 **Tests conditions**	最小 **Min**	典型 **Typ**	最大 **Max**	单位 **Units**
关态特性 **Off –Characteristics**						
漏一源击穿电压 Drain-Source Voltage	BV_{DSS}	I_D=250μA, V_{GS}=0V	85	95	-	V
击穿电压温度特性 Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	I_D=250μA, referenced to 25℃	-	0.08	-	V/℃
零栅压下漏极漏电流 Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=85V,V_{GS}=0V, T_C=25℃	-	-	1	μA
		V_{DS}=68V, T_C=125℃	-	-	100	μA
栅极体漏电流 Gate-body leakage current	I_{GSS}（F/R）	V_{DS}=0V, V_{GS} =±20V	-	-	±100	nA
通态特性 **On-Characteristics**						
阈值电压 Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = VGS , I_D=250μA	2	-	4	V
静态导通电阻 Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS} =10V , I_D=50A	-	5.3	6.5	mΩ
正向跨导 Forward Transconductance	gfs	V_{DS} = 10V, I_D=50A（note 4）	-	65	-	S
动态特性 **Dynamic Characteristics**						
栅电阻 Gate Resistance	Rg	f=1.0MHz,V DS OPEN	-	1.5	-	Ω
输入电容 Input capacitance	Ciss	V_{DS}=40V, V_{GS} =0V, f=1.0MHz	-	3374	-	pF
输出电容 Output capacitance	Coss		-	507	-	
反向传输电容 Reverse transfer capacitance	Crss		-	18	-	
开关特性 **Switching Characteristics**						
延迟时间 Turn-On delay time	td(on)	V_{DD}=40V, I_D=50A, R_G=20Ω V_{GS} =10V （note 4，5）	-	37	-	ns
上升时间 Turn-On rise time	tr		-	30	-	ns
延迟时间 Turn-Off delay time	td(off)		-	37	-	ns
下降时间 Turn-Off Fall time	tf		-	20	-	ns
栅极电荷总量 Total Gate Charge	Qg	V_{DS} =40V , I_D=50A , V_{GS} =10V （note 4，5）	-	67	-	nC
栅一源电荷 Gate-Source charge	Qgs		-	19	-	nC
栅一漏电荷 Gate-Drain charge	Qgd		-	37	-	nC
漏一源二极管特性及最大额定值 **Drain-Source Diode Characteristics and Maximum Ratings**						
正向最大连续电流 Maximum Continuous Drain -Source Diode Forward Current	I_S		-	-	80	A
正向最大脉冲电流 Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}		-	-	320	A
正向压降 Drain-Source Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=50A	-	-	1.2	V
反向恢复时间 Reverse recovery time	trr	V_{GS}=0V, I_S=30A ,dI_F/dt=100A/μs (note 4)	-	48	-	ns
反向恢复电荷 Reverse recovery charge	Qrr		-	115	-	nC

N-CHANNEL MOSFET /N沟道增强型场效应晶体管
RCP100N8F6A/RCS100N8F6A/RCD100N8F6A

热特性 THERMAL CHARACTERISTIC

项目 Parameter	符号 Symbol	RCP/D100N8F6A	RCS100N8F6A	单位 Unit
结到管壳的热阻 Thermal Resistance, Junction to Case	Rth(j-c)	0.8		℃/W
结到环境的热阻 Thermal Resistance, Junction to Ambient	Rth(j-A)	62.5		℃/W

注释:
1：脉冲宽度由最高结温限制
2：L=1mH, I_{AS}=20A, V_{DD}=48V, R_G=25 Ω,起始结温 T_J=25℃
3：I_{SD} ≤80A,di/dt ≤300A/μs,V_{DD}≤BV_{DSS},起始结温 T_J=25℃
4：脉冲测试：脉冲宽度 ≤300μs,占空比≤2%
5：基本与工作温度无关

Notes:
1：Pulse width limited by maximum junction temperature
2：L=1mH, I_{AS}=20A, V_{DD}=48V, R_G=25 Ω,Starting T_J=25℃
3：I_{SD} ≤80A,di/dt ≤300A/μs,V_{DD}≤BV_{DSS}, Starting T_J=25℃
4：Pulse Test：Pulse Width ≤300μs,Duty Cycle≤2%
5：Essentially independent of operating temperature

N-CHANNEL MOSFET /N沟道增强型场效应晶体管
RCP100N8F6A/RCS100N8F6A/RCD100N8F6A

Typical Performance Characteristics

Figure 1. Safe Operating Area

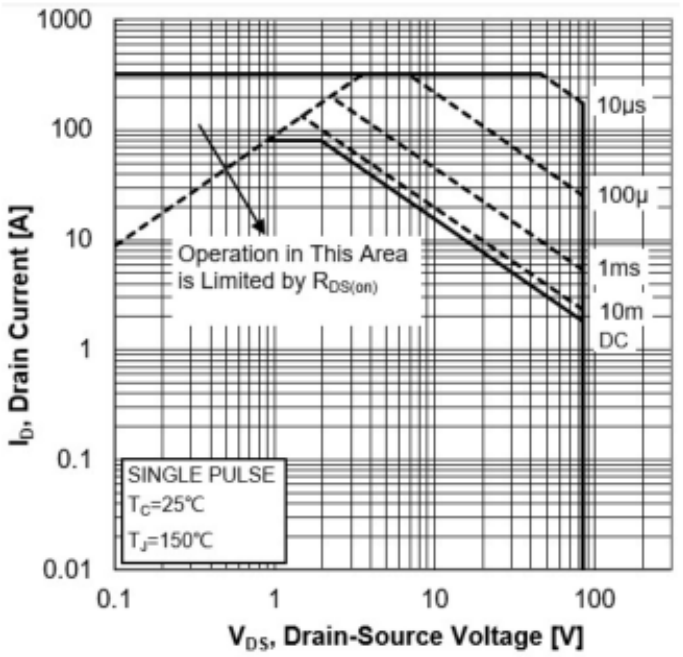


Figure 2. Maximum Power Dissipation vs Case Temperature

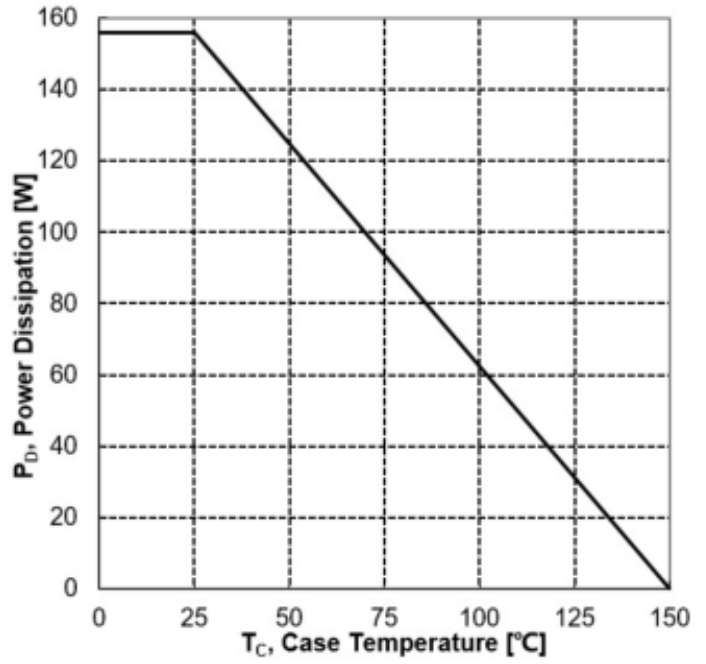


Figure 3. Maximum Continuous Drain Current vs Case Temperature

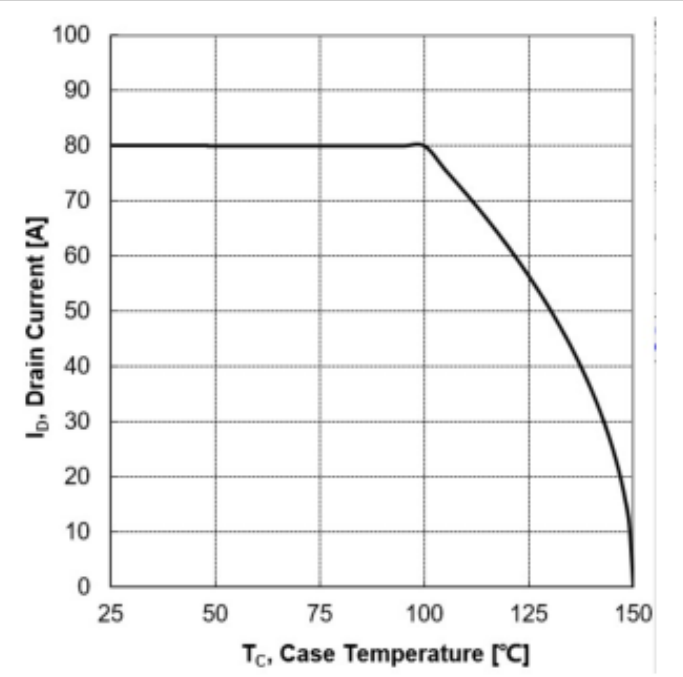


Figure 4. Typical Output Characteristics

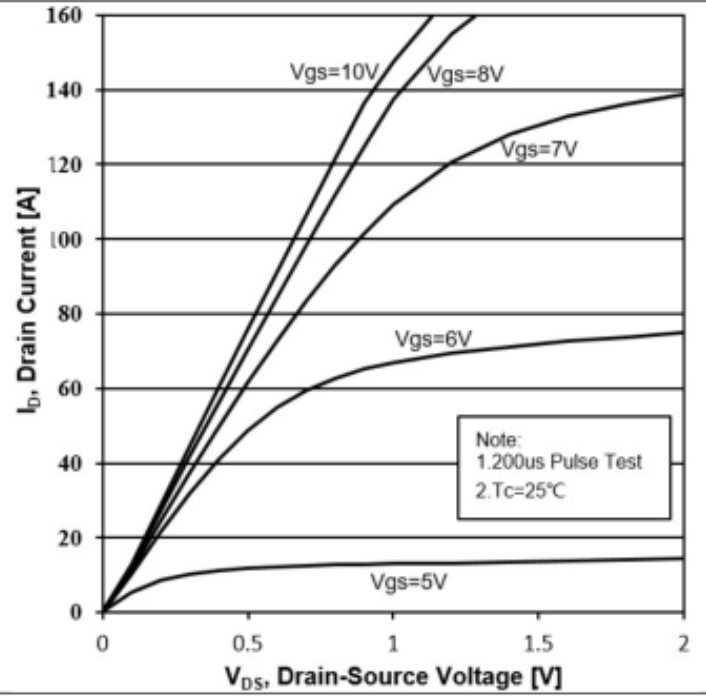
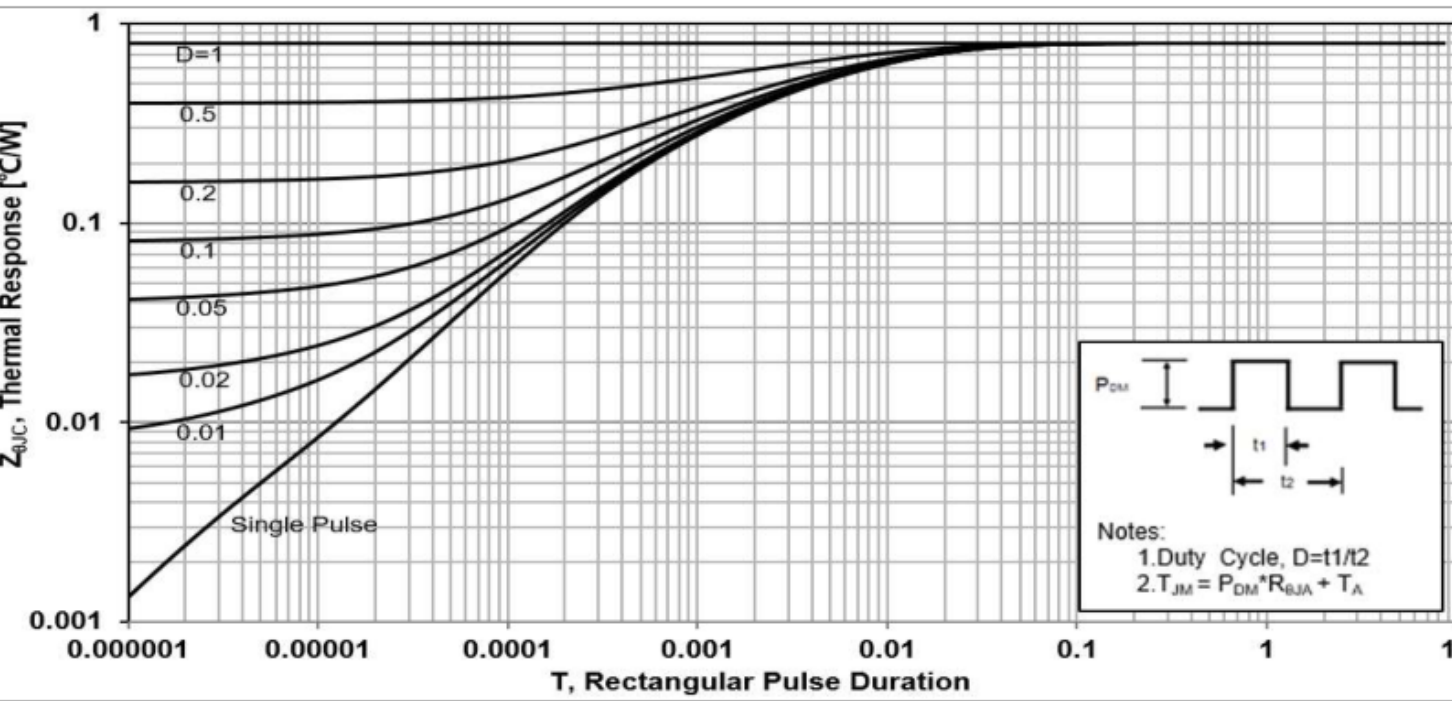


Figure 5. Transient Thermal Impedance



N-CHANNEL MOSFET /N沟道增强型场效应晶体管
RCP100N8F6A/RCS100N8F6A/RCD100N8F6A

Figure 6. Typical Transfer Characteristics

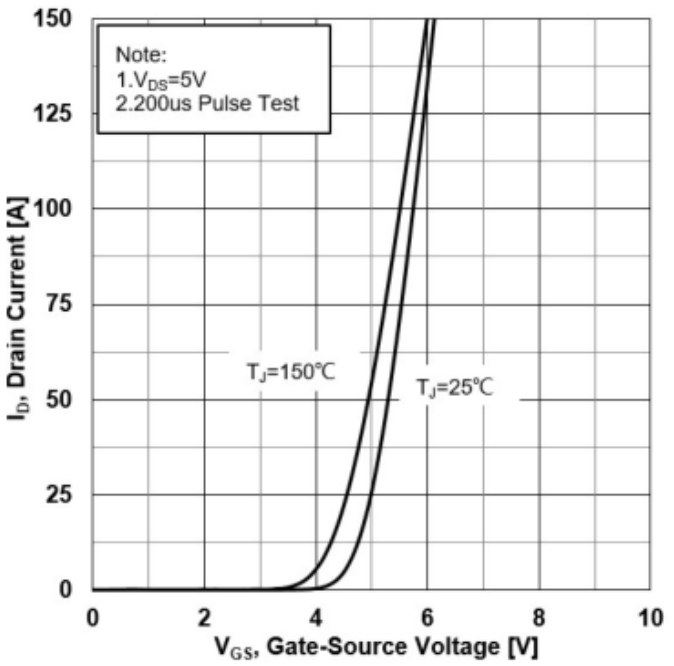


Figure 7. Source-Drain Diode Forward Characteristics

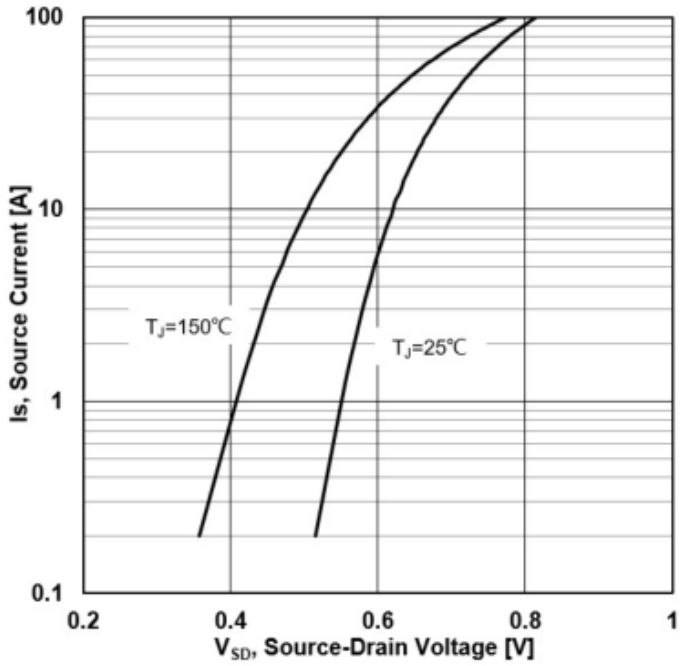


Figure 8. Drain-Source On-Resistance vs Drain Current

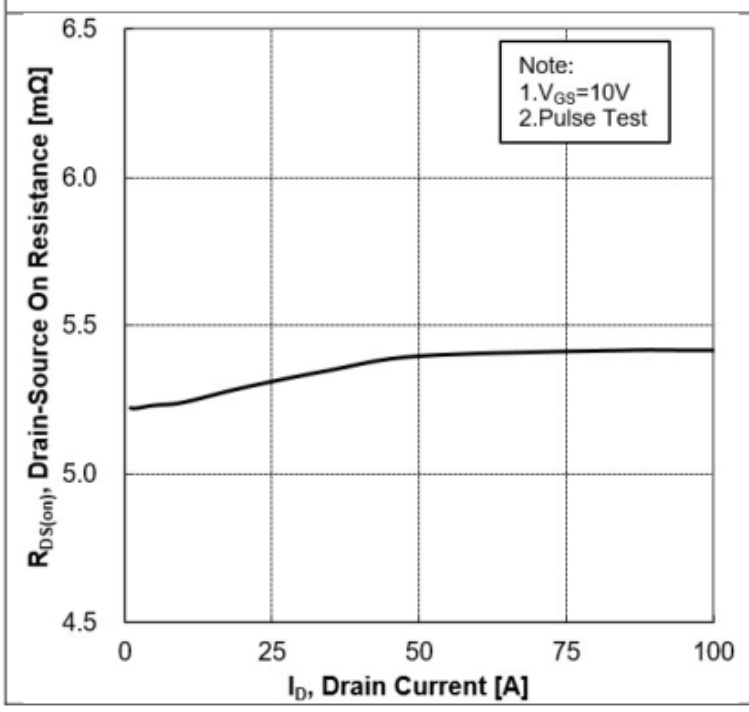


Figure 9. Normalized On-Resistance vs Junction Temperature

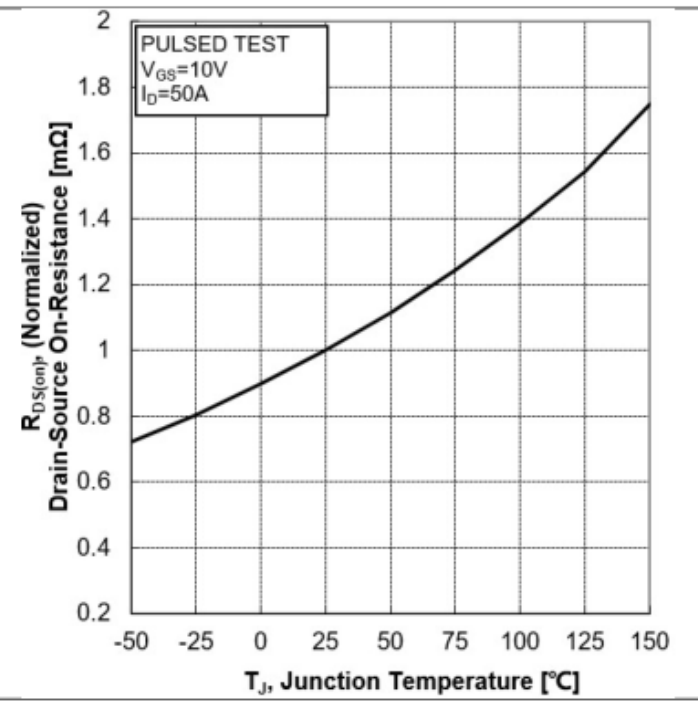


Figure 10. Normalized Threshold Voltage vs Junction Temperature

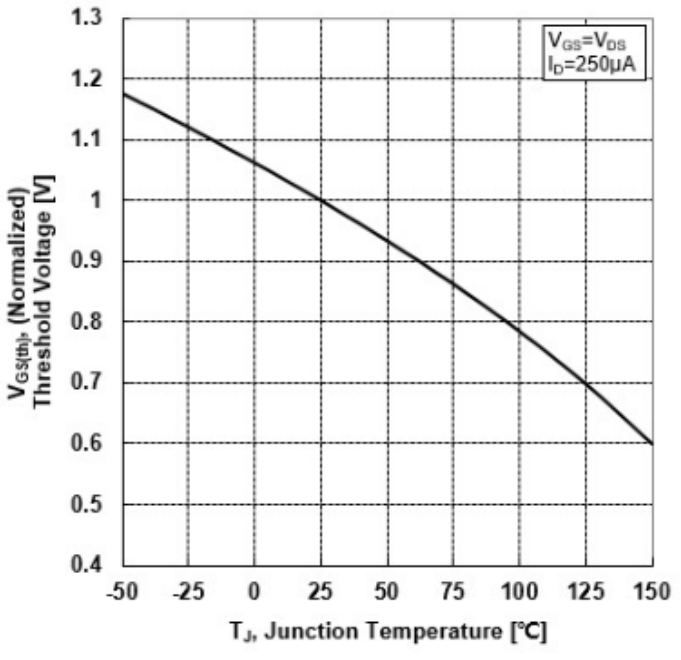
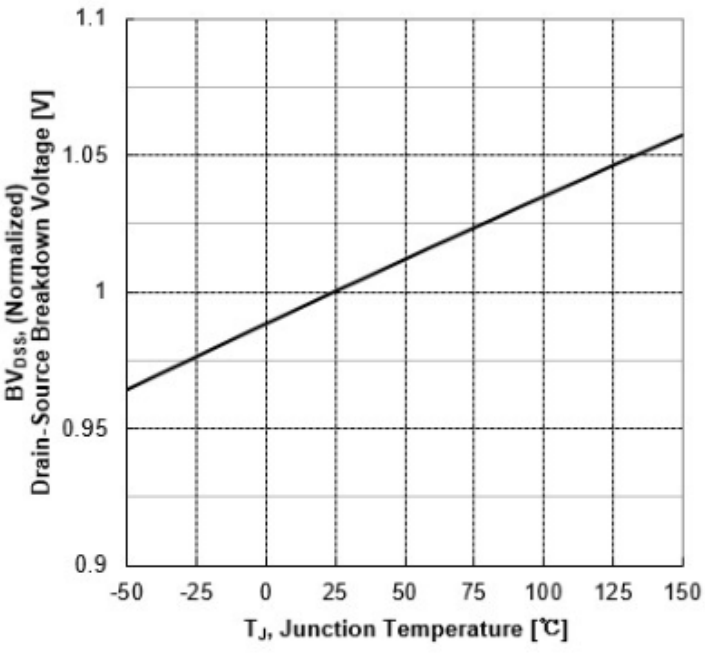


Figure 11. Normalized Breakdown Voltage vs Junction Temperature



N-CHANNEL MOSFET /N沟道增强型场效应晶体管
RCP100N8F6A/RCS100N8F6A/RCD100N8F6A

Figure 12. Capacitance Characteristics

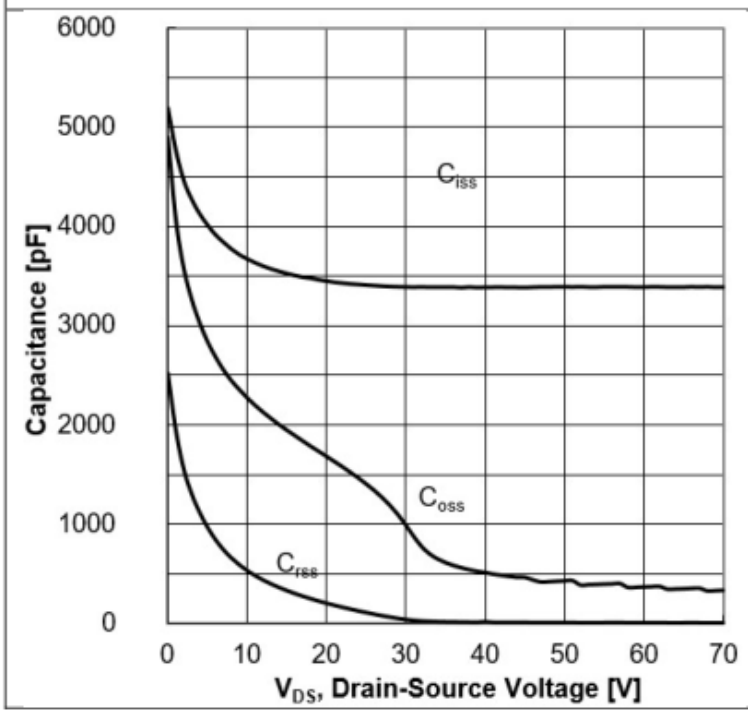
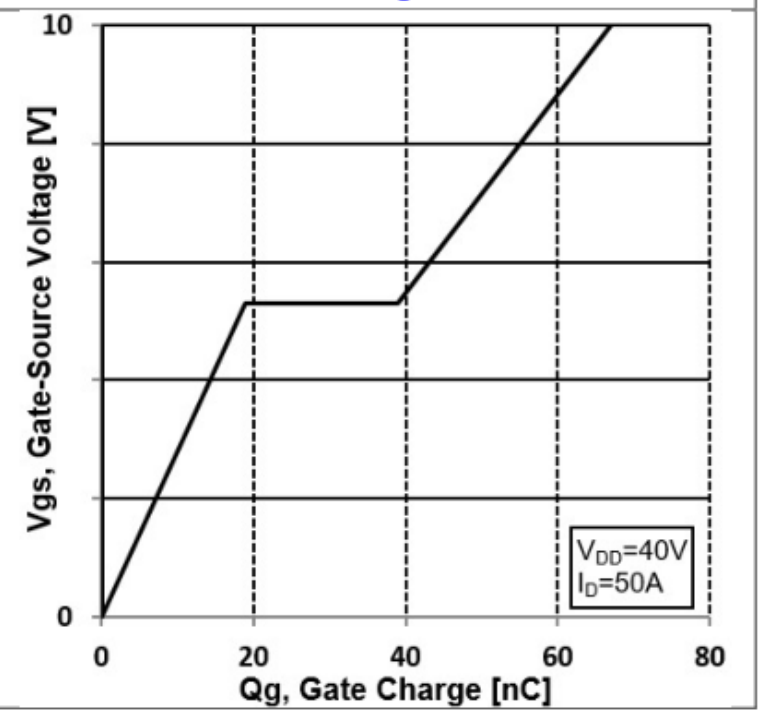


Figure 13. Typical Gate Charge vs Gate-Source Voltage



N-CHANNEL MOSFET /N沟道增强型场效应晶体管
RCP100N8F6A/RCS100N8F6A/RCD100N8F6A

Test Circuit & Waveform

Figure 14. Resistive Switching Test Circuit

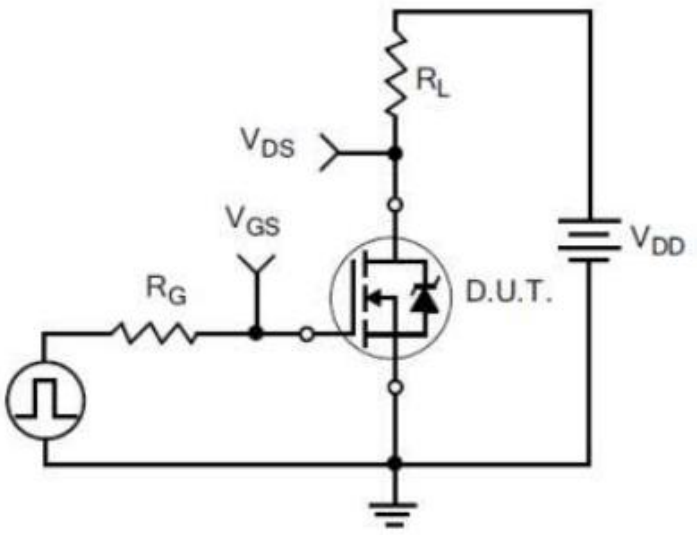


Figure 15. Resistive Switching Waveforms

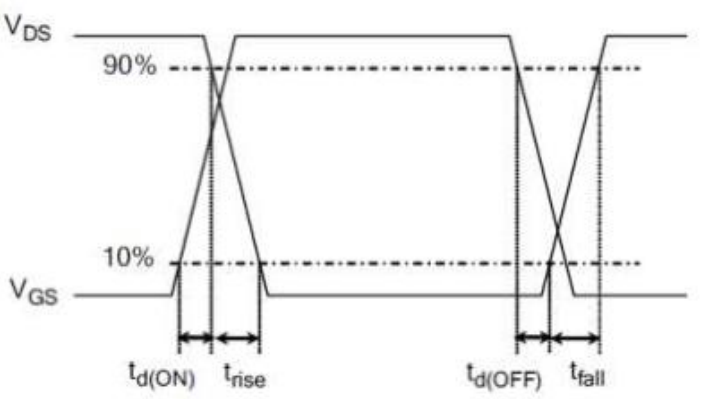


Figure 16. Gate Charge Test Circuit

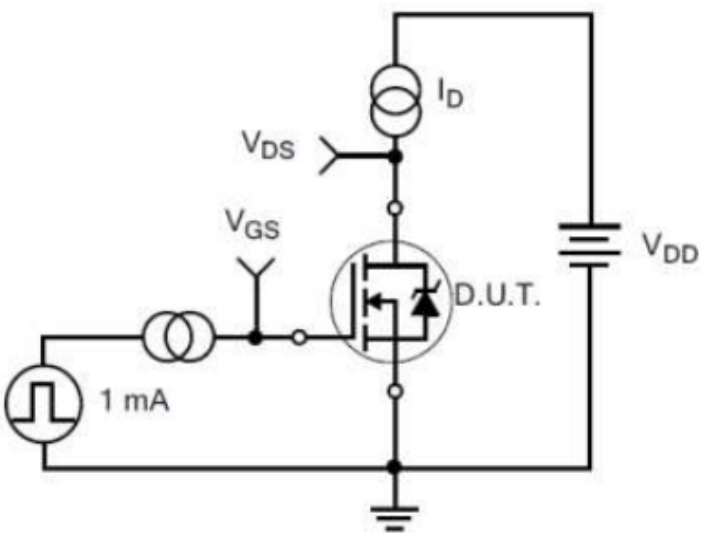


Figure 17. Gate Charge Waveforms

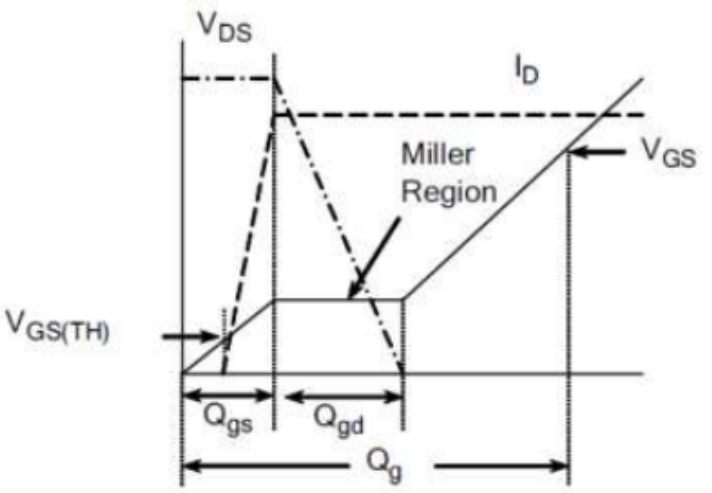


Figure 18. Diode Reverse Recovery Test Circuit

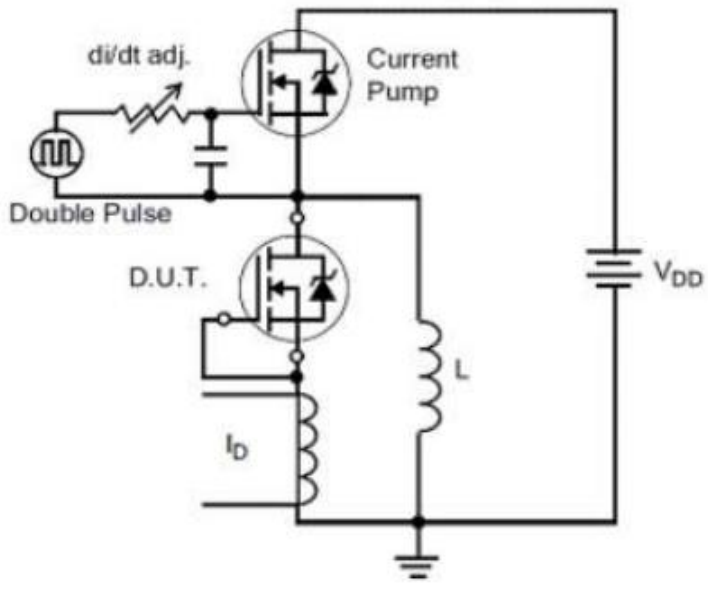
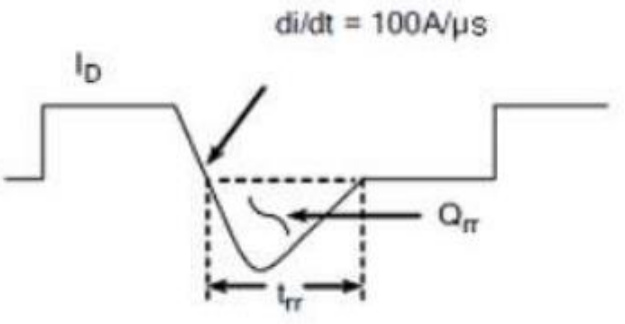
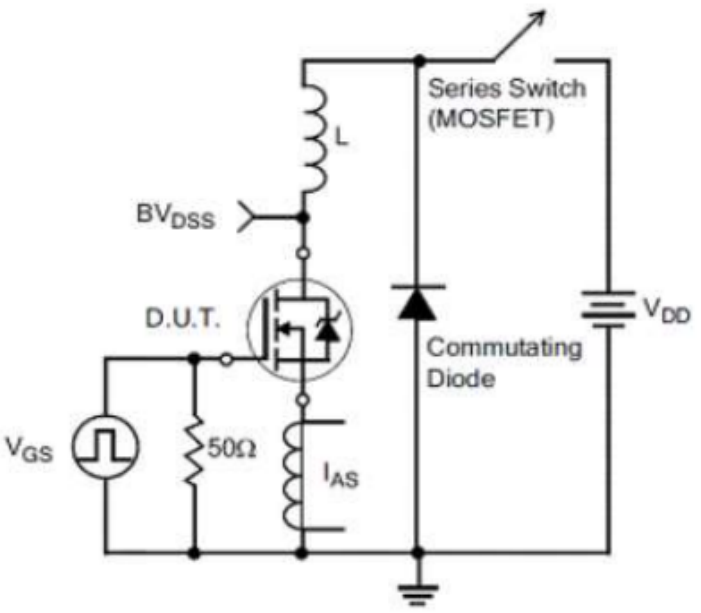
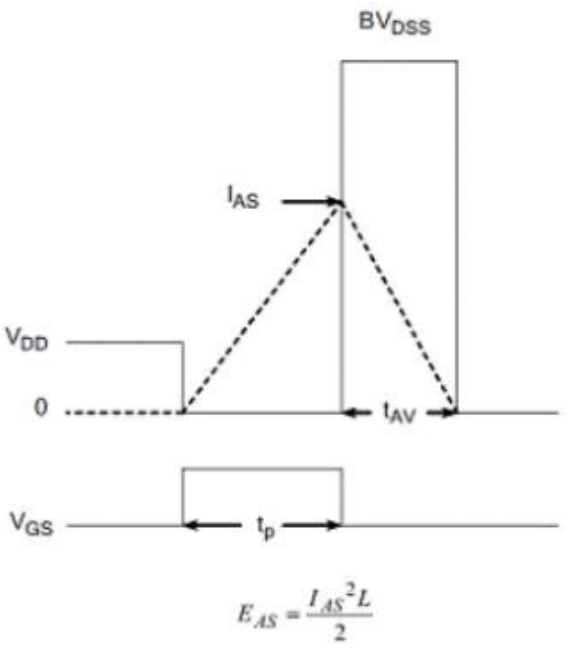


Figure 19. Diode Reverse Recovery Waveform

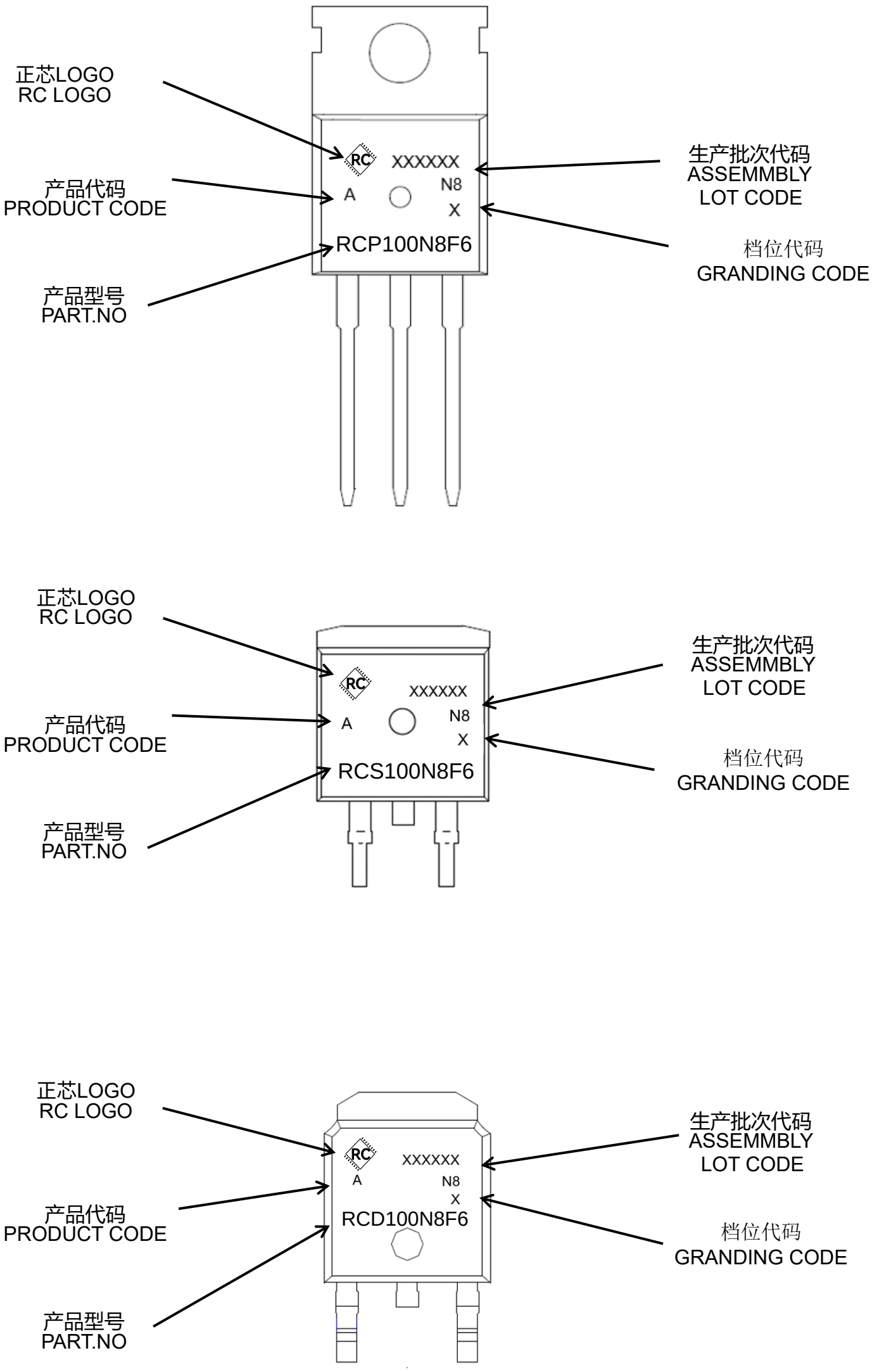


N-CHANNEL MOSFET /N沟道增强型场效应晶体管
RCP100N8F6A/RCS100N8F6A/RCD100N8F6A

Figure 20. Unclamped Inductive Switching Test Circuit	Figure 21. Unclamped Inductive Switching Waveform
	

N-CHANNEL MOSFET /N沟道增强型场效应晶体管
RCP100N8F6A/RCS100N8F6A/RCD100N8F6A

印记 Marking:

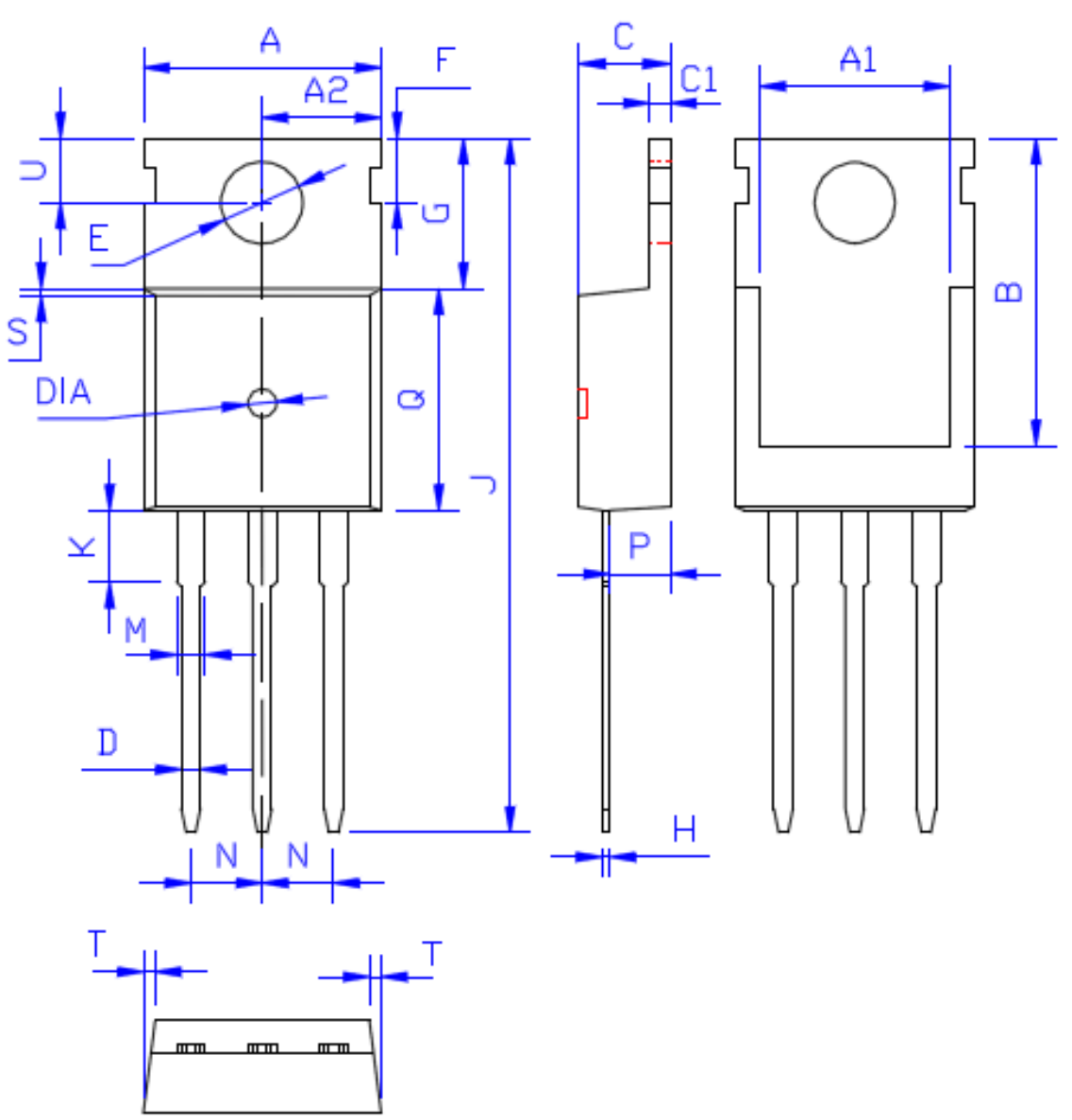


N-CHANNEL MOSFET /N沟道增强型场效应晶体管
RCP100N8F6A/RCS100N8F6A/RCD100N8F6A

外形尺寸：

Package Dimension：

TO-220



DIM	MILLIMETERS
A	10.00±0.30
A1	8.00±0.30
A2	5.00±0.30
B	13.20±0.40
C	4.50±0.20
C1	1.30±0.20
D	0.80±0.20
E	3.60±0.20
F	3.00±0.30
G	6.60±0.40
H	0.50±0.20
J	28.88±0.50
K	3.00±0.30
M	1.30±0.30
N	Typical 2.54
P	2.40±0.40
Q	9.20±0.40
S	0.25±0.15
T	0.25±0.15
U	2.80±0.30
DIA	宽 1.50±0.10 深 0.50 MAX

（Unit：mm）

N-CHANNEL MOSFET /N沟道增强型场效应晶体管
RCP100N8F6A/RCS100N8F6A/RCD100N8F6A

外形尺寸：

Package Dimension：

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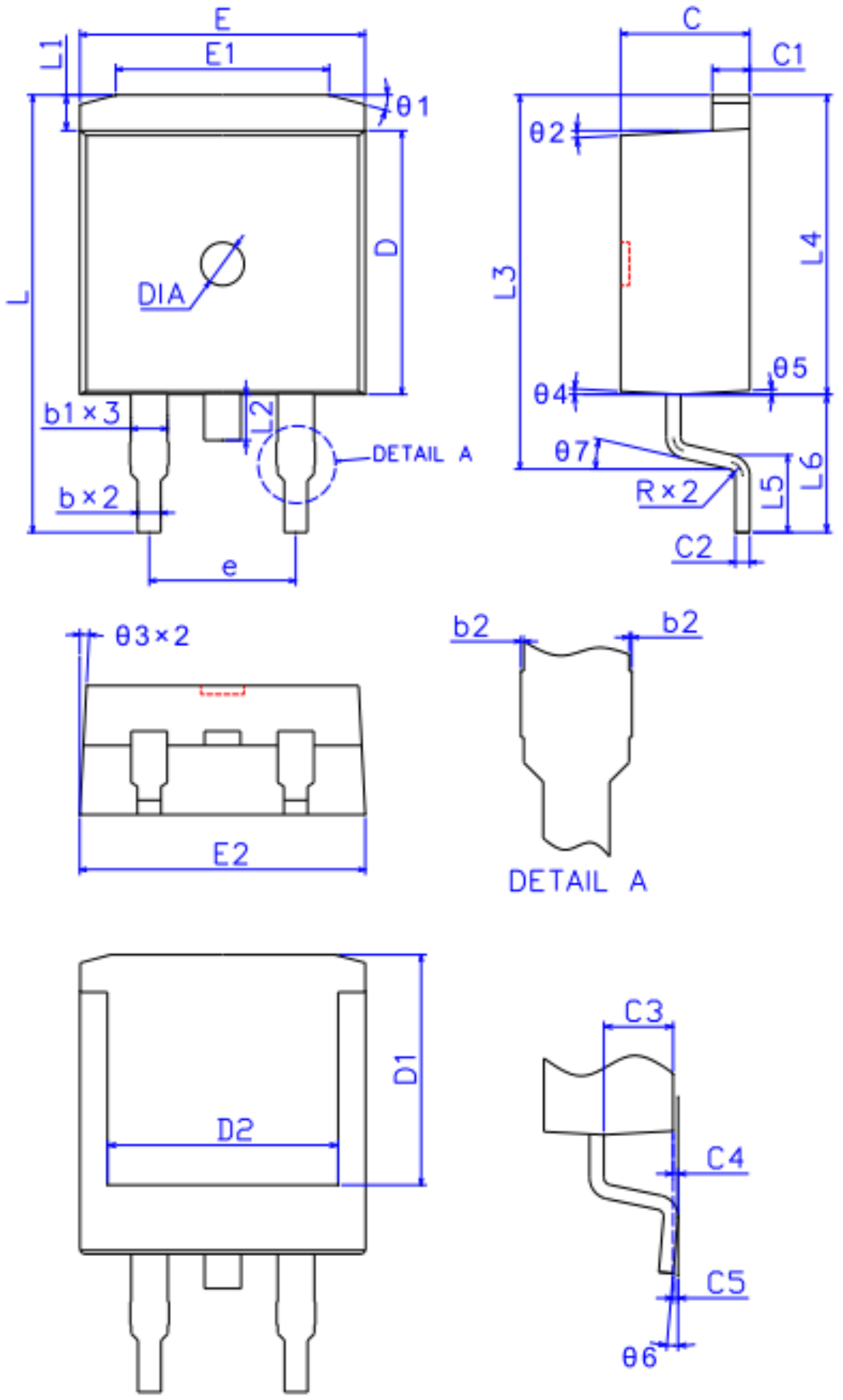

标注	尺寸(mm)
E	9.88±0.10
E1	7.40±0.20
E2	9.90±0.15
L	15.20±0.25
L1	1.30±0.15
L2	1.60±0.10
L3	13.00±0.20
L4	10.40±0.15
L5	2.60±0.15
L6	4.80±0.20
b	0.80±0.07
b1	1.27±0.07
b2	0.05±0.07
C	4.48±0.10
C1	1.30±0.07
C2	0.50±0.07
C3	2.40±0.06
C4	0.10±0.08
C5	0.10±0.08
D	9.20±0.10
D1	8.00±0.10
D2	8.00±0.10
R	0.50±0.10
θ1	15° ±2°
θ2	3° ±2°
θ3	3° ±2°
θ4	3° ±2°
θ5	3° ±2°
θ6	0° ~6°
θ7	13° ±2°
e	5.08±0.10
DIA	宽 1.50±0.10 深 0.30±0.15

N-CHANNEL MOSFET /N沟道增强型场效应晶体管
RCP100N8F6A/RCS100N8F6A/RCD100N8F6A

外形尺寸：

Package Dimension：

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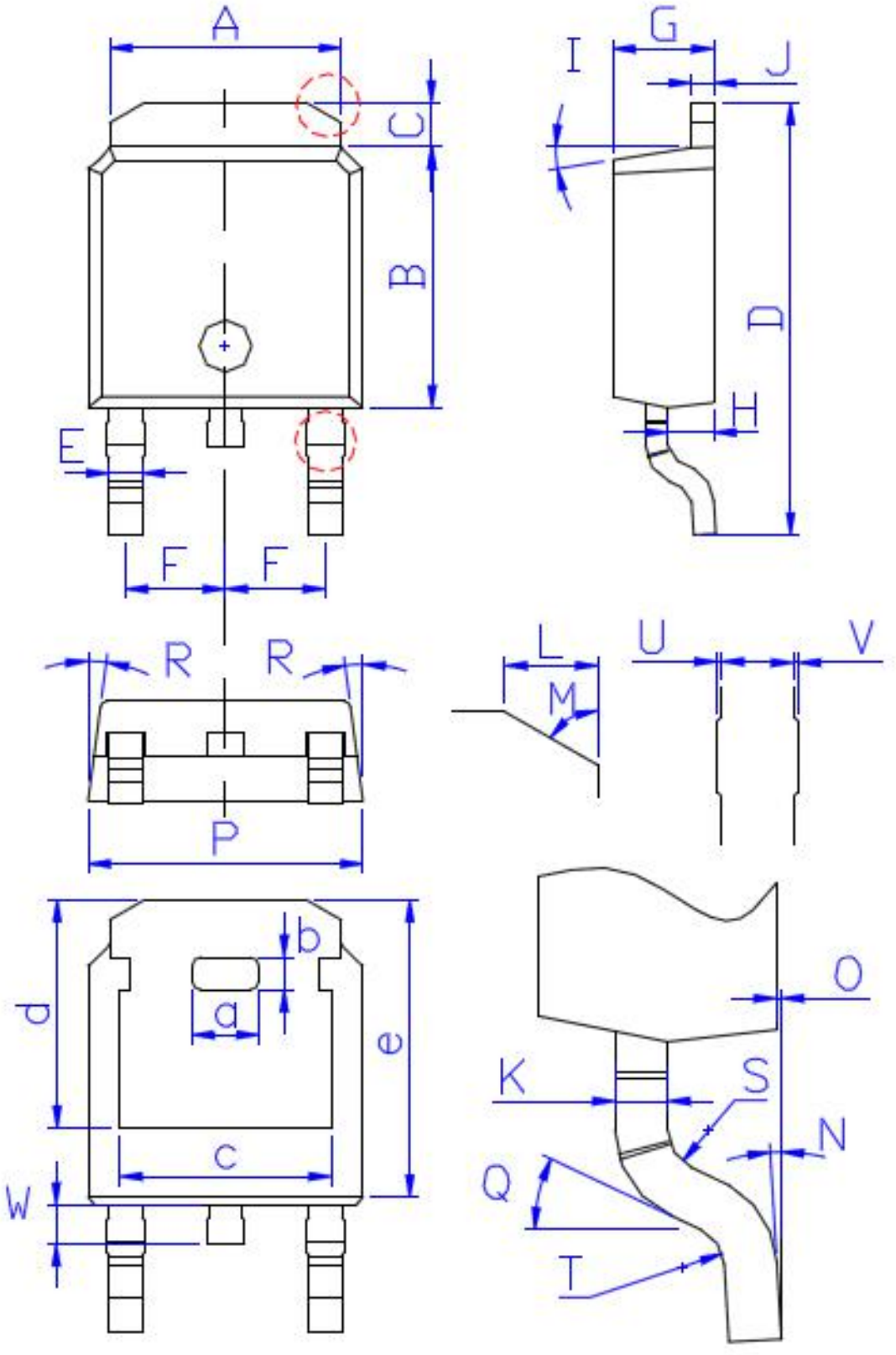

DIM	MILLIMETERS
A	5.34±0.30
B	6.00±0.30
C	1.05±0.30
D	9.95±0.30
E	0.76±0.15
F	2.28±0.15
G	2.30±0.30
H	1.06±0.30
I	(4-10)°
J	0.51±0.15
K	0.52±0.15
L	0.80±0.30
M	60°
N	(0-10)°
O	0.05±0.05
P	6.60±0.30
Q	25°
R	(4-8.5)°
S	R0.40
T	R0.40
U	0.05±0.05
V	0.05±0.05
W	0.90±0.30
a	1.80±0.30
b	0.75±0.30
c	4.85±0.30
d	5.30±0.30
e	6.90±0.30

(Units: mm)